

Fig. 1(a)

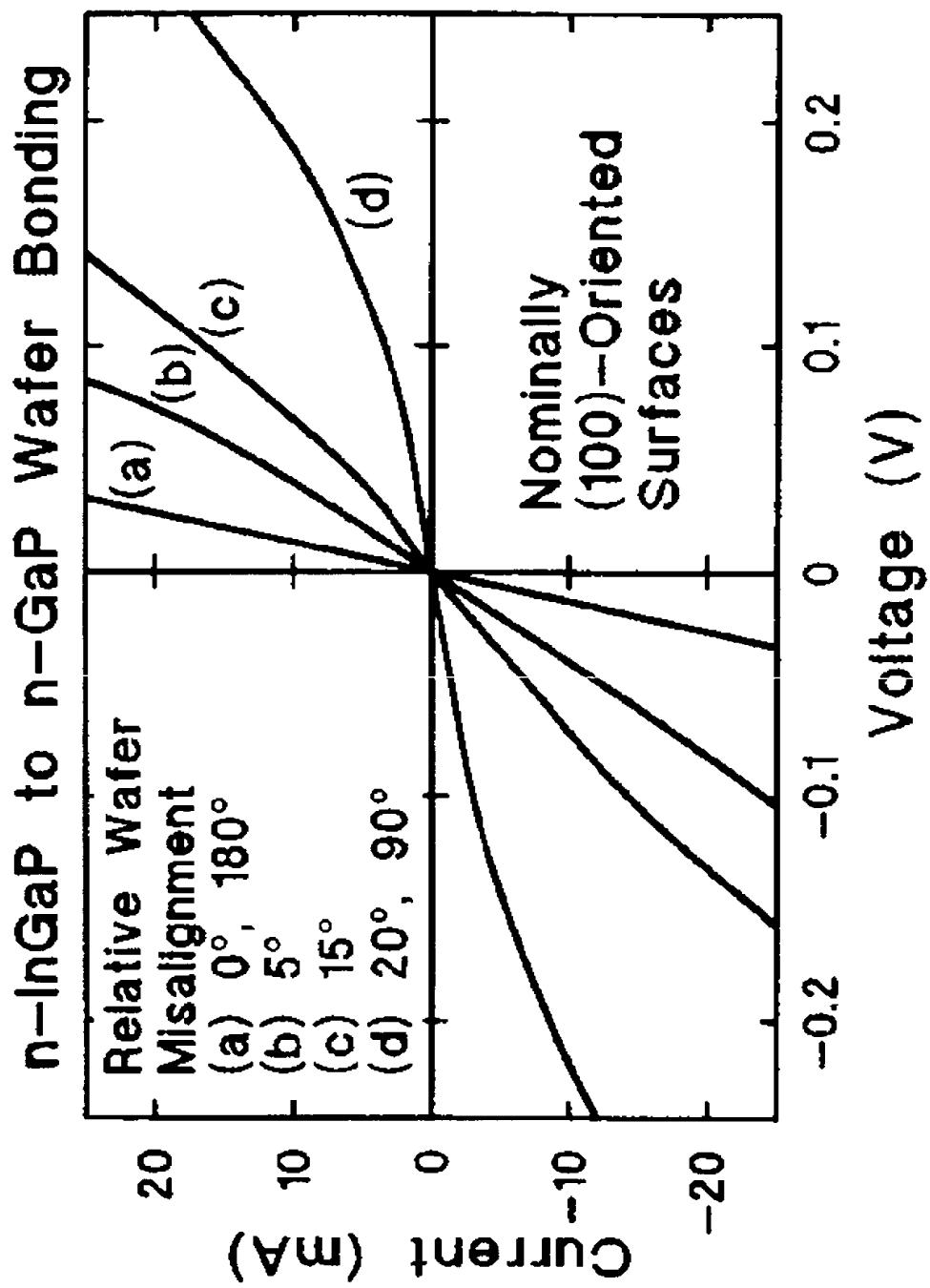


Fig. 1 (b)

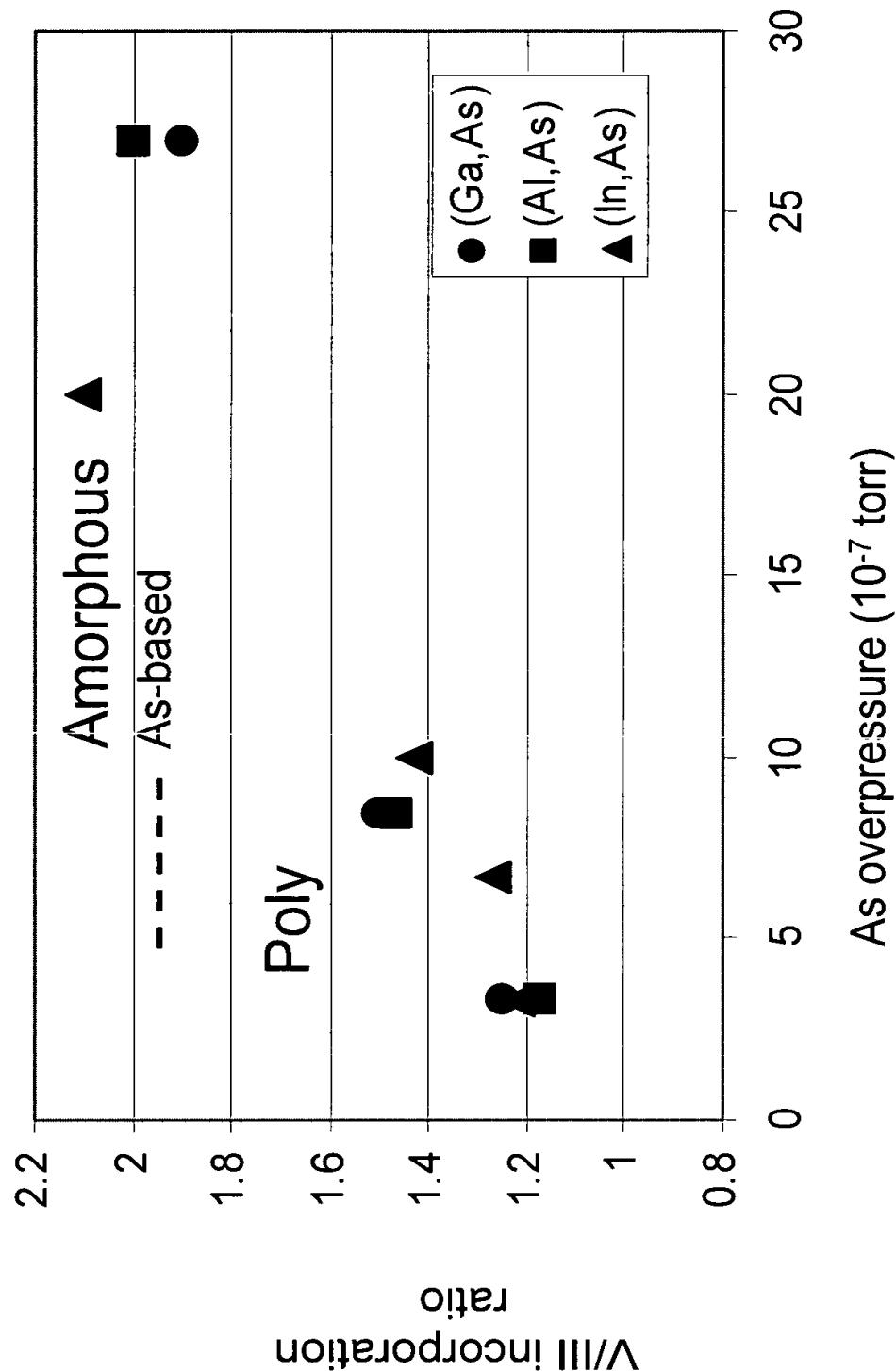


Fig. 2(a)

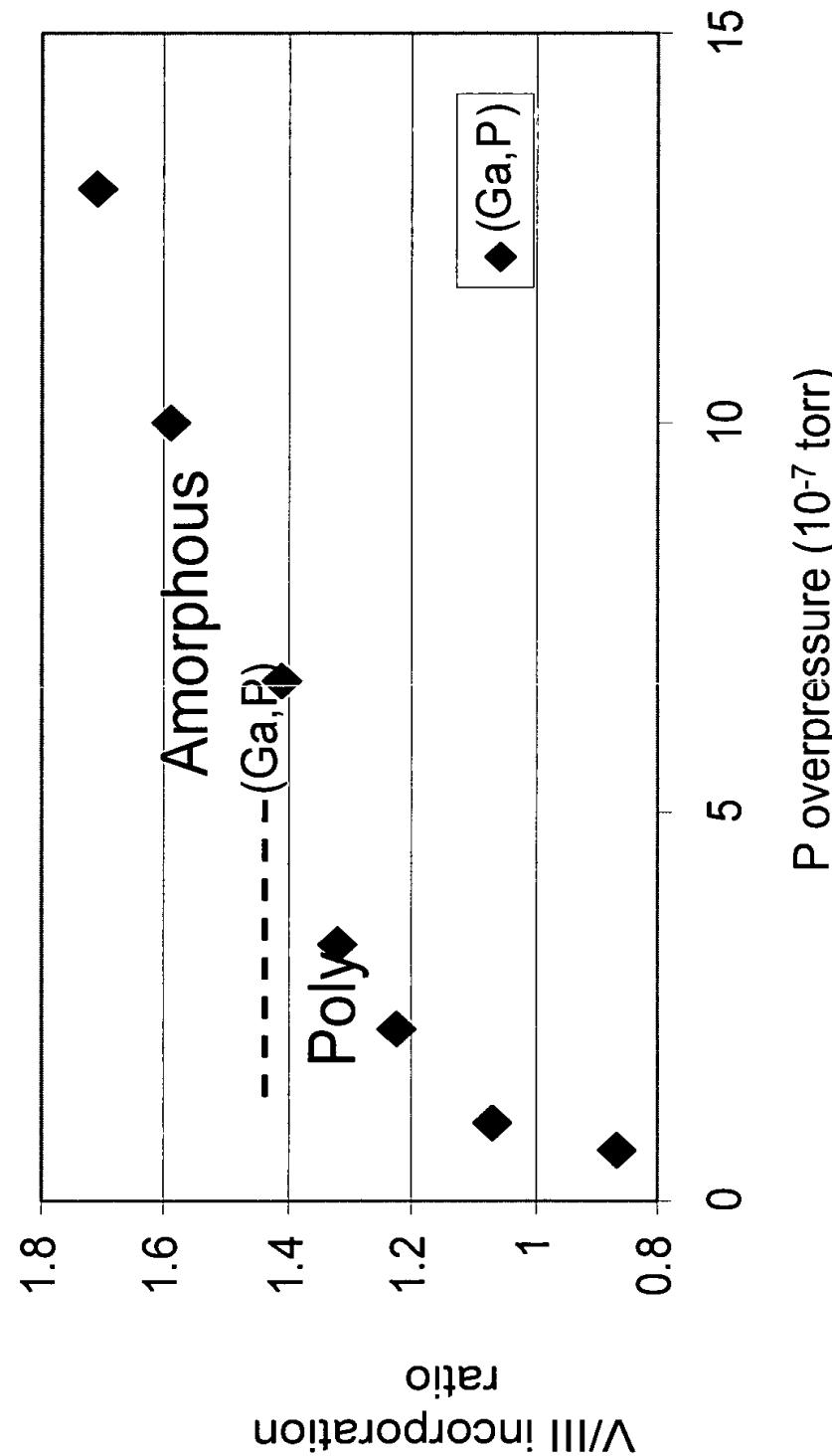
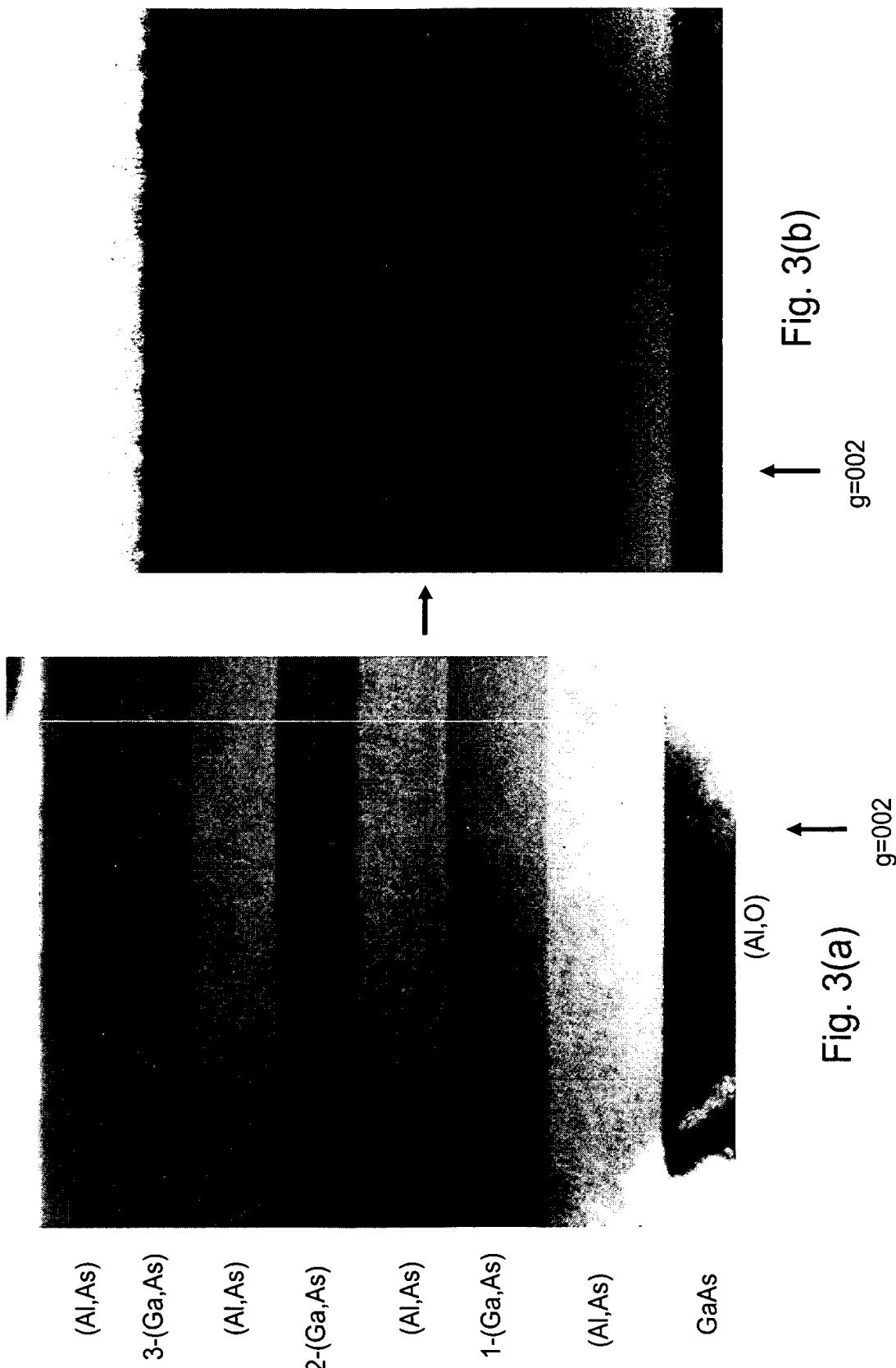


Fig. 2(b)



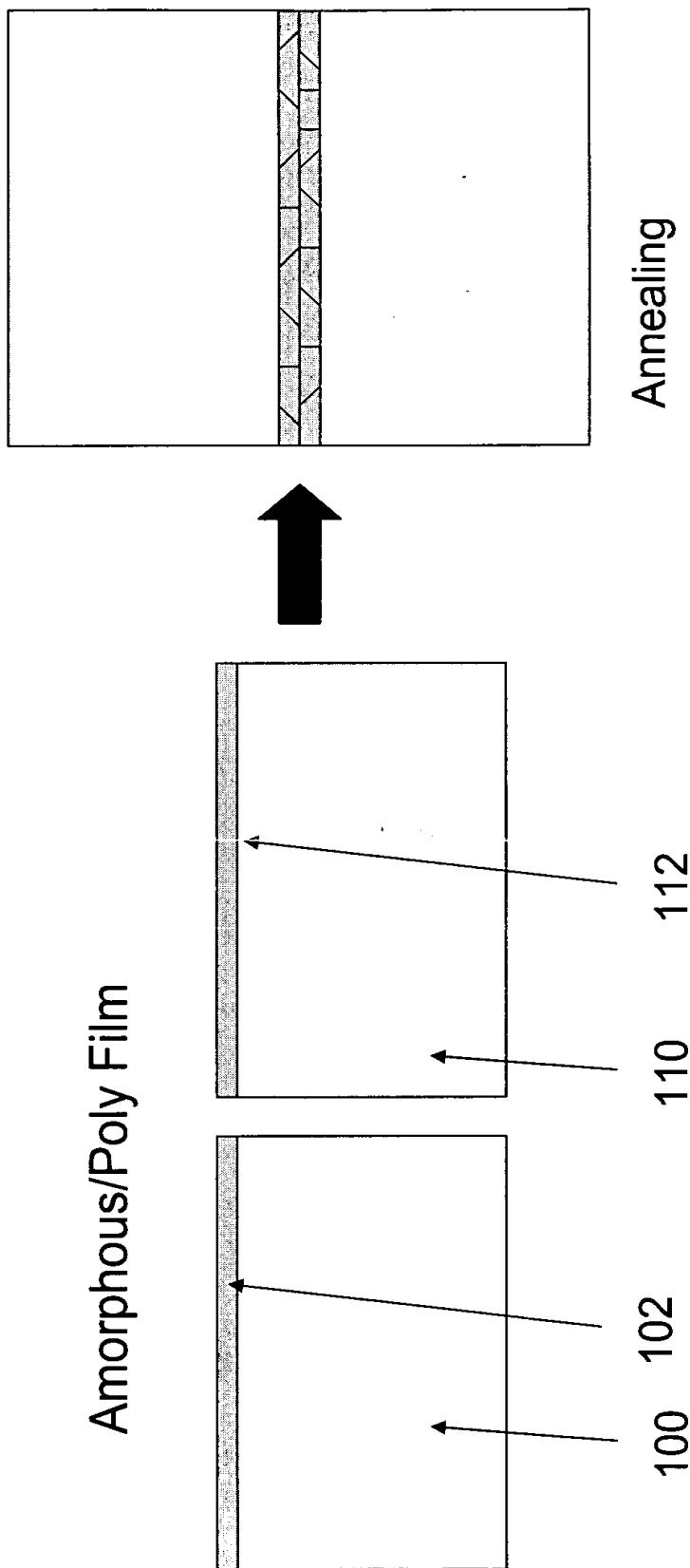


Fig. 4

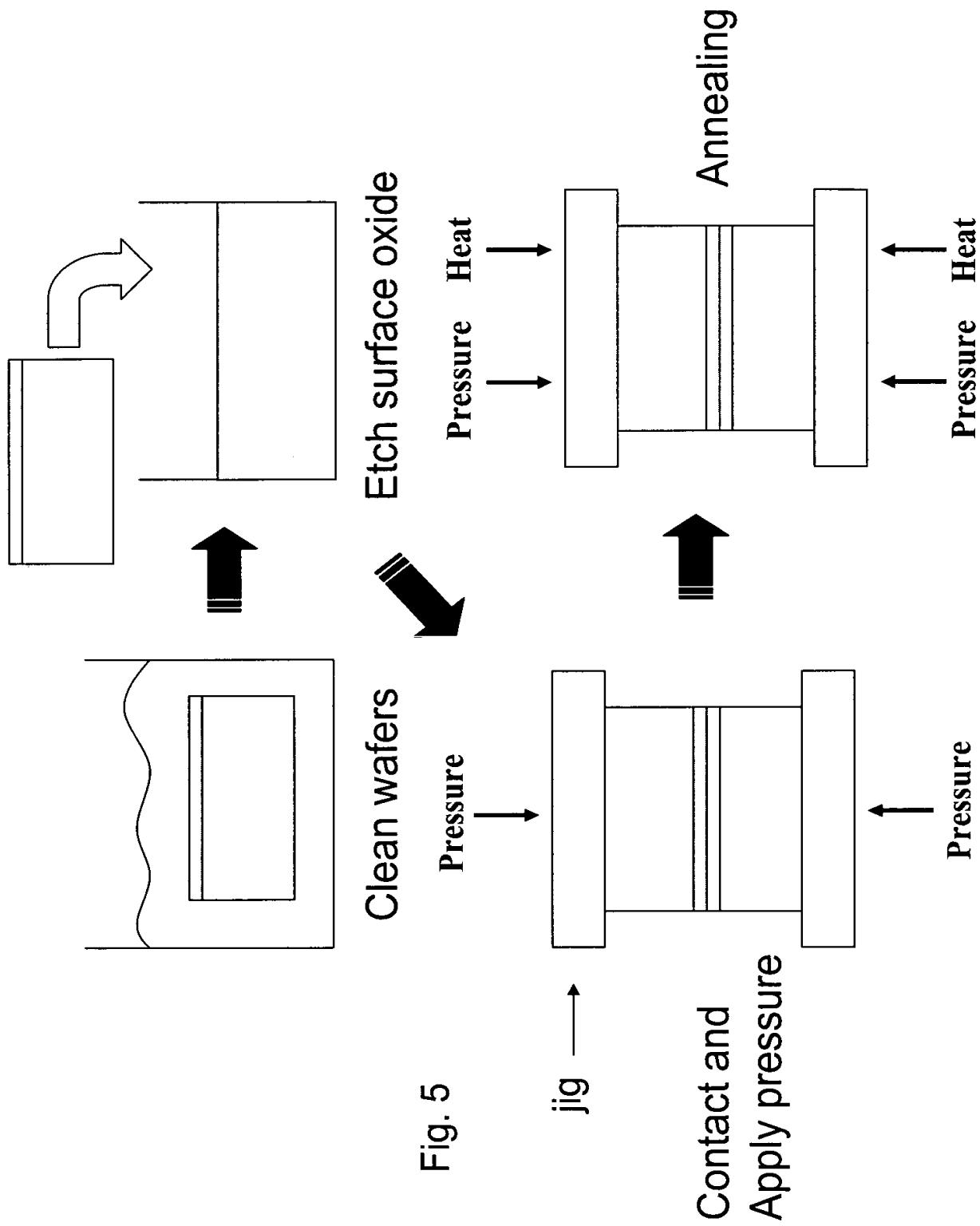


Fig. 5

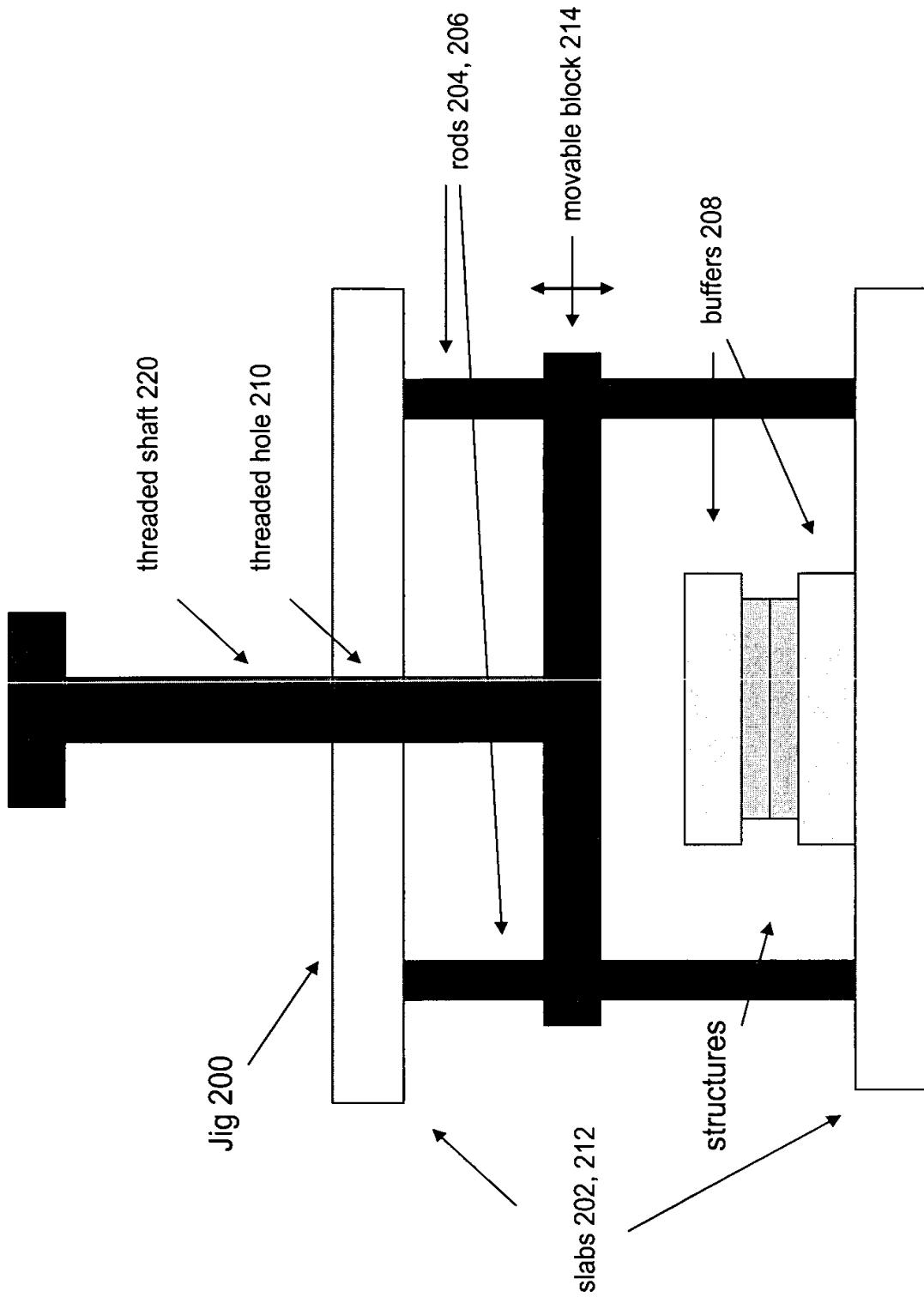
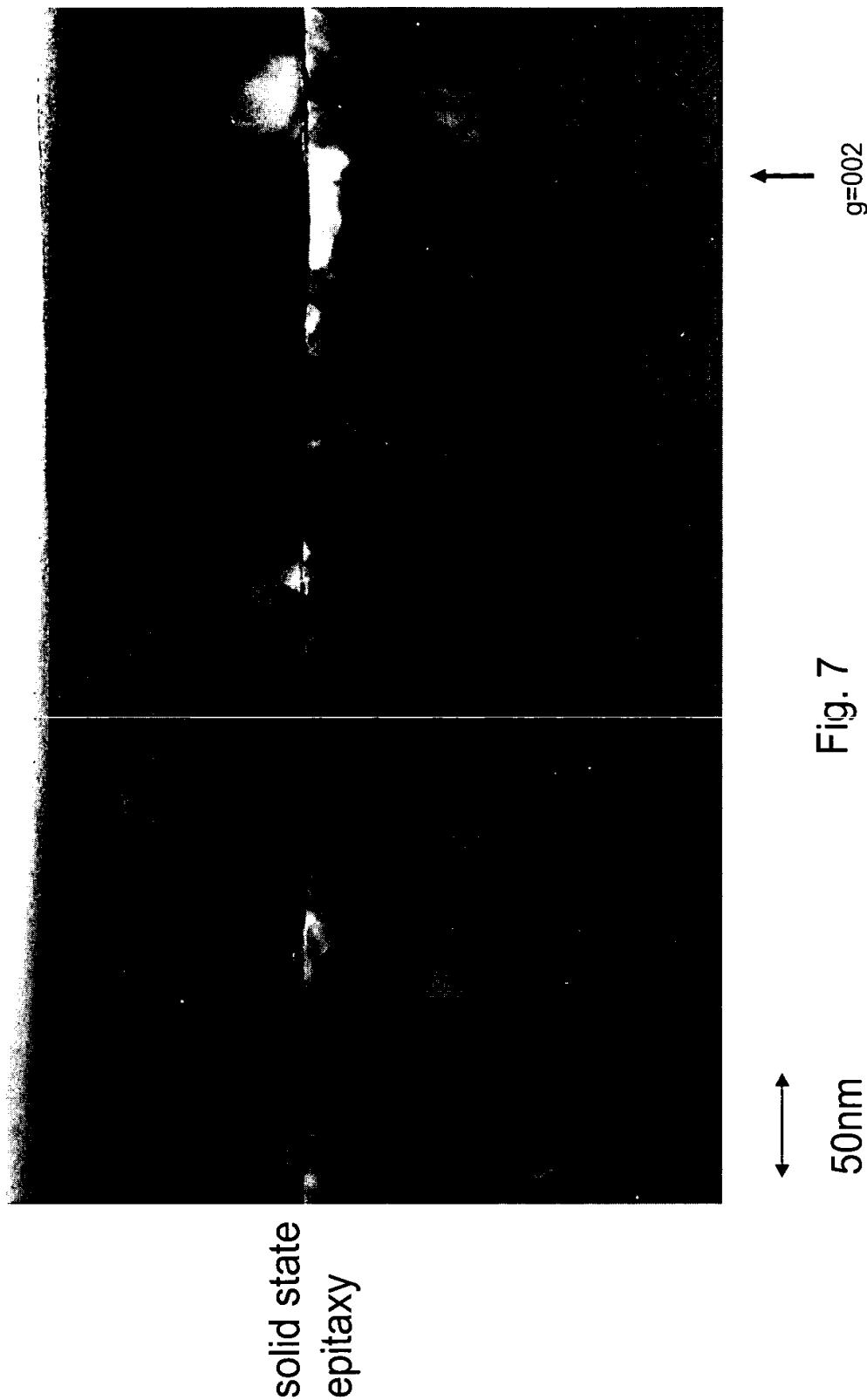


Fig. 6



Polycrystalline (Ga,P) bonding
Anneal at 600 °C for 9 hrs

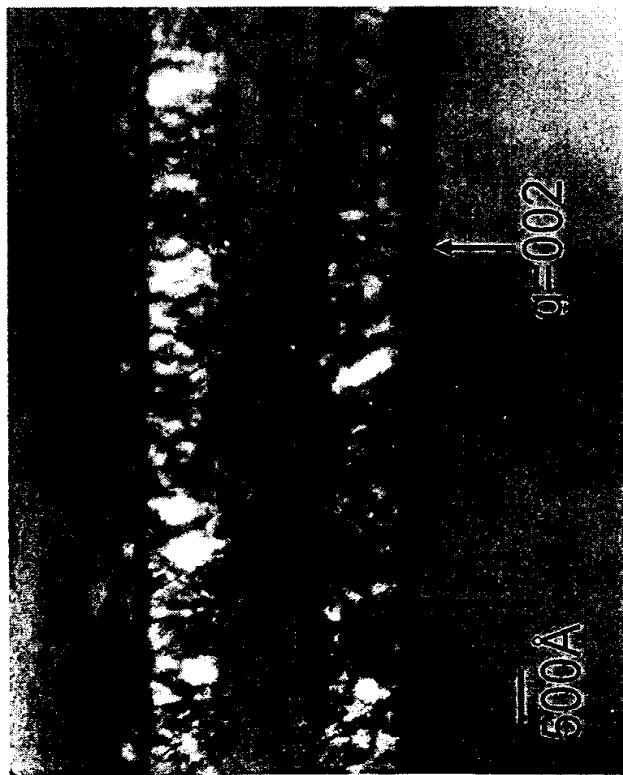


Fig. 8(a)

Amorphous (Ga,P) bonding
Anneal at 600 °C for 10 hrs

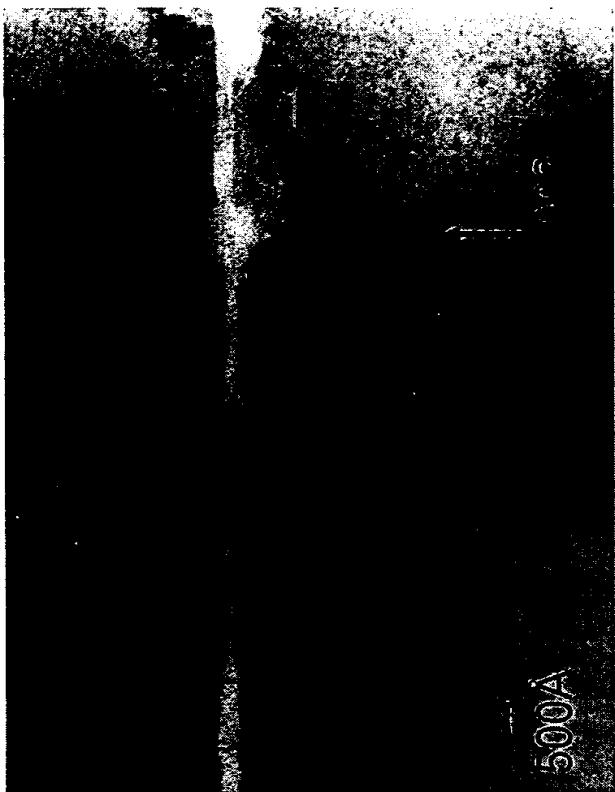


Fig. 8(b)

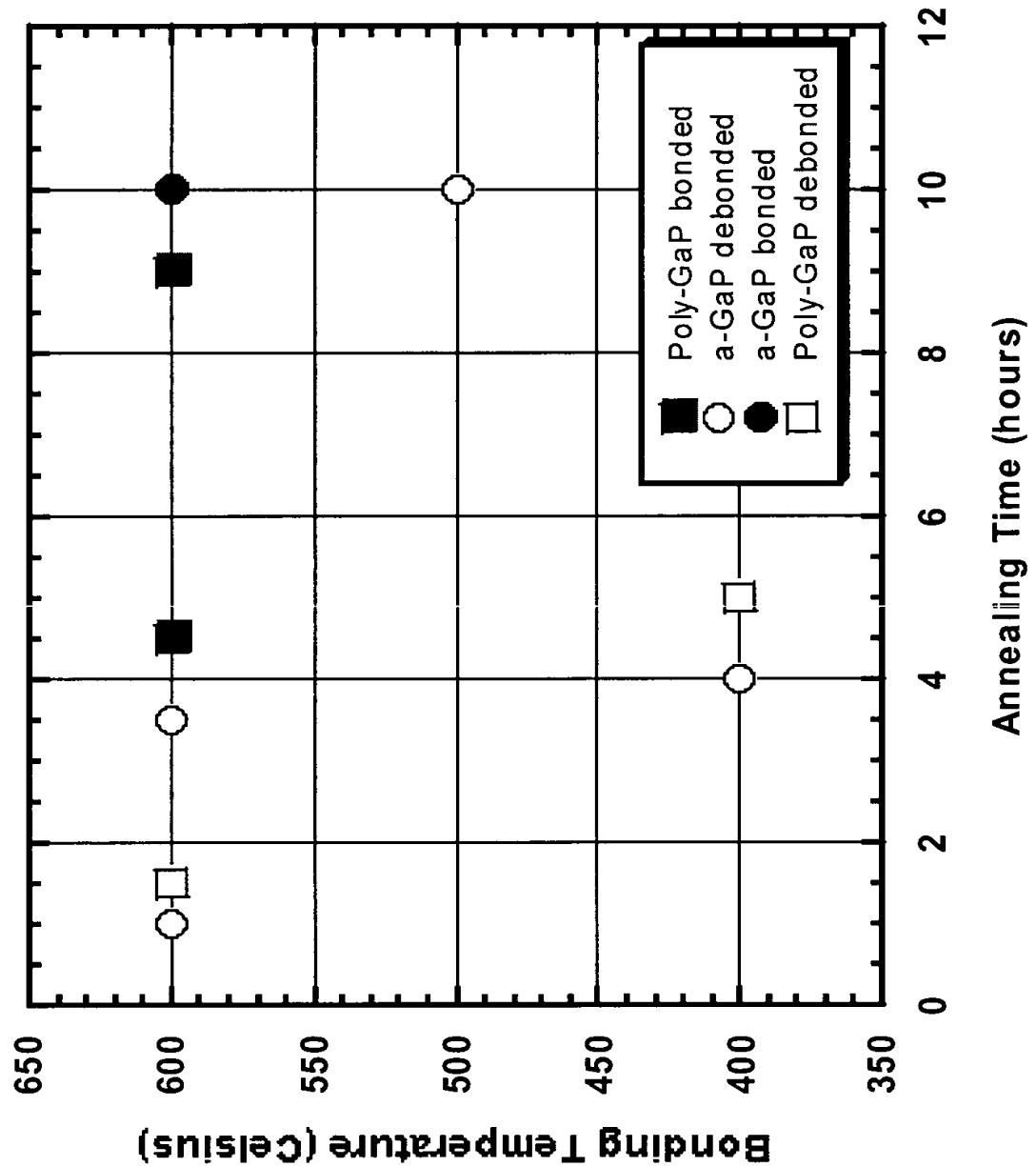


Fig. 9

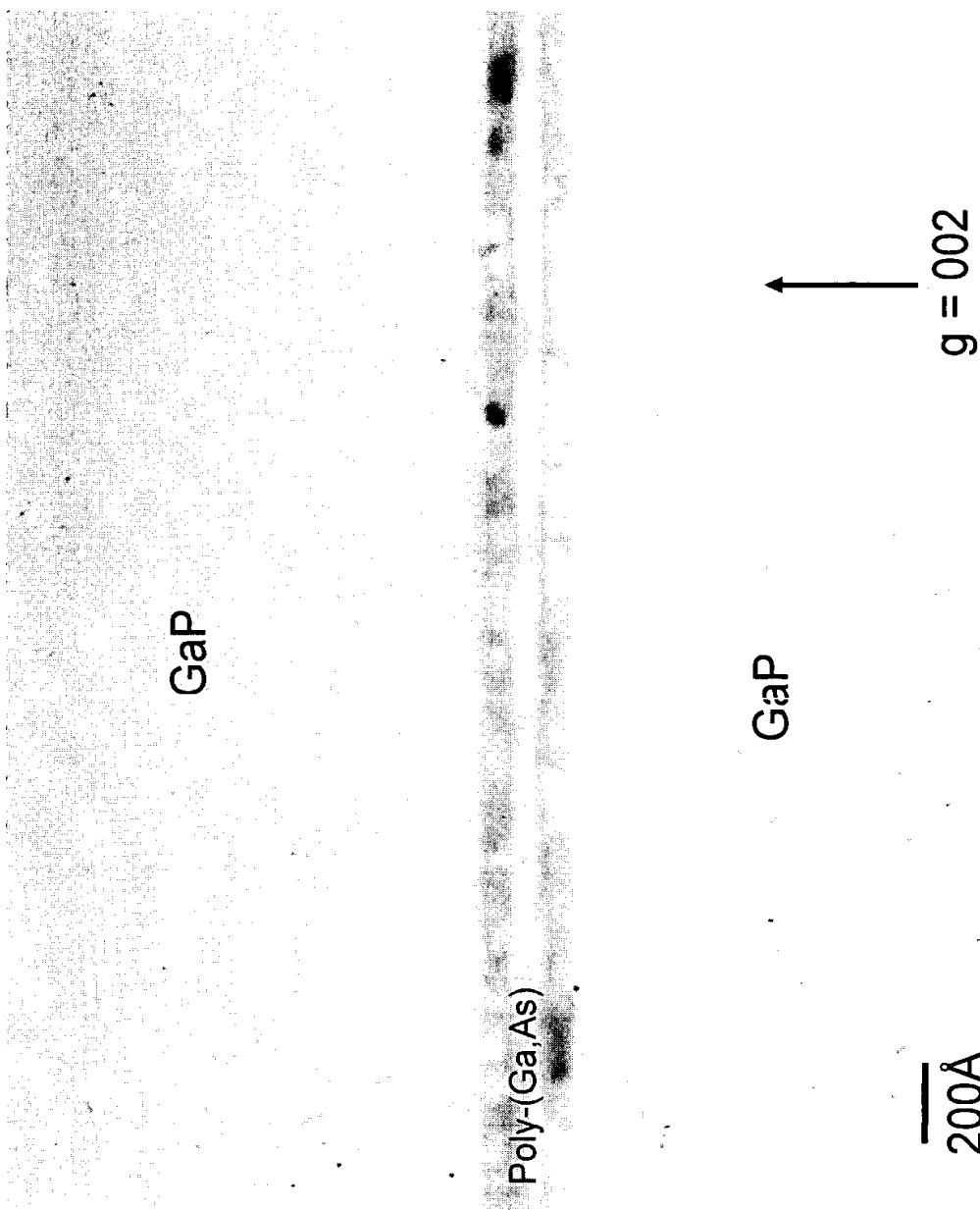
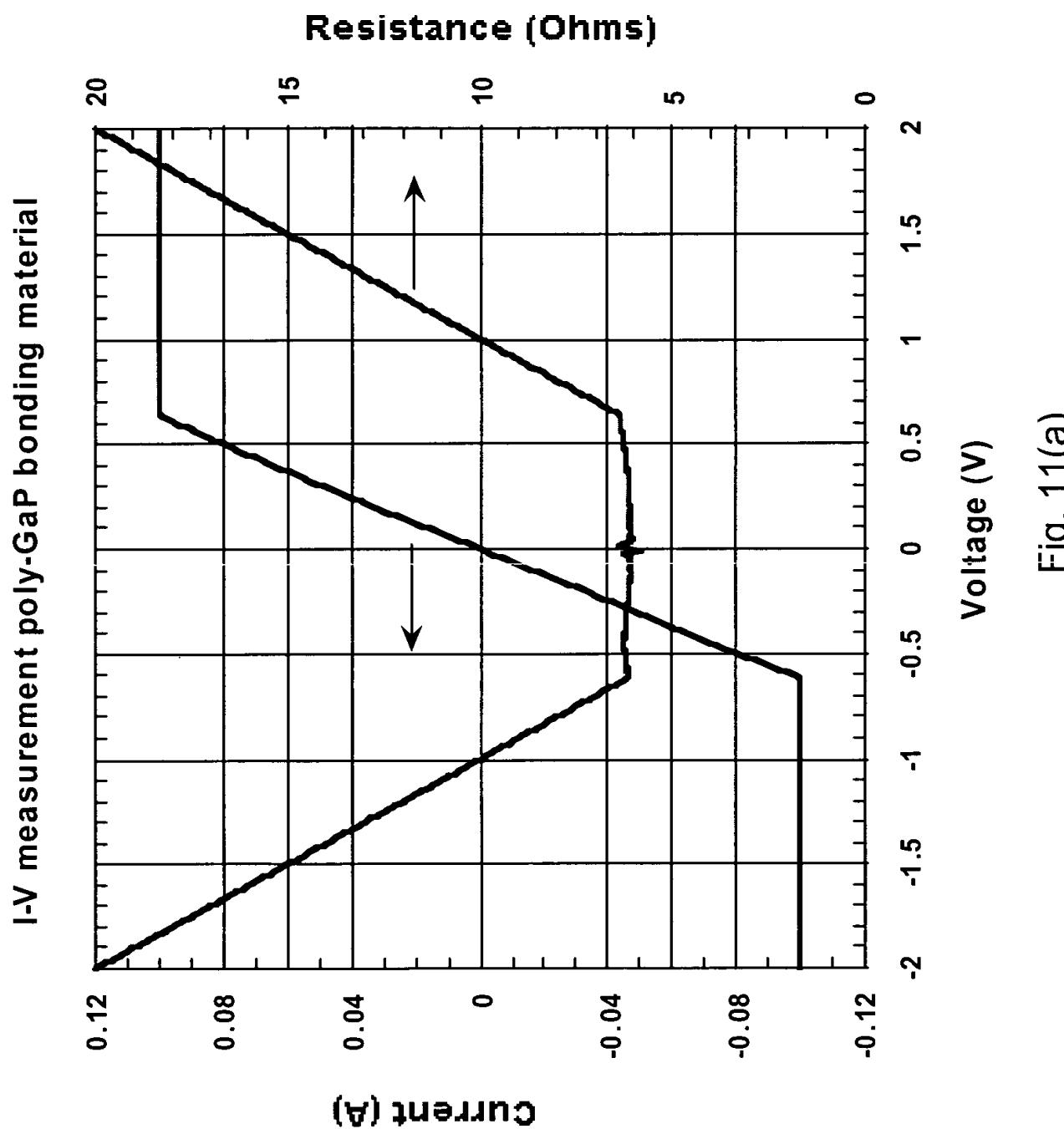


Fig. 10



I-V measurement amorphous GaP bonding material

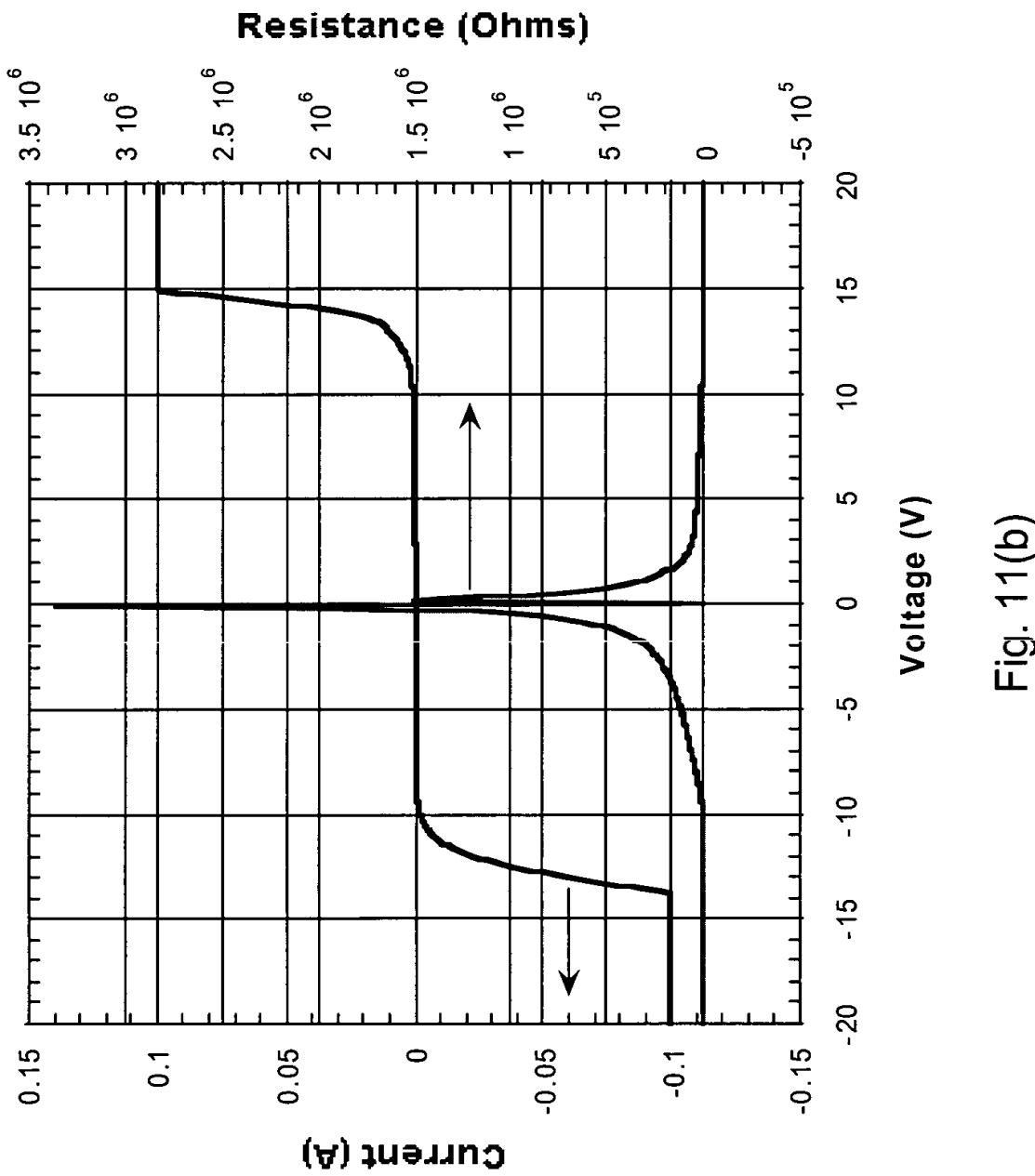
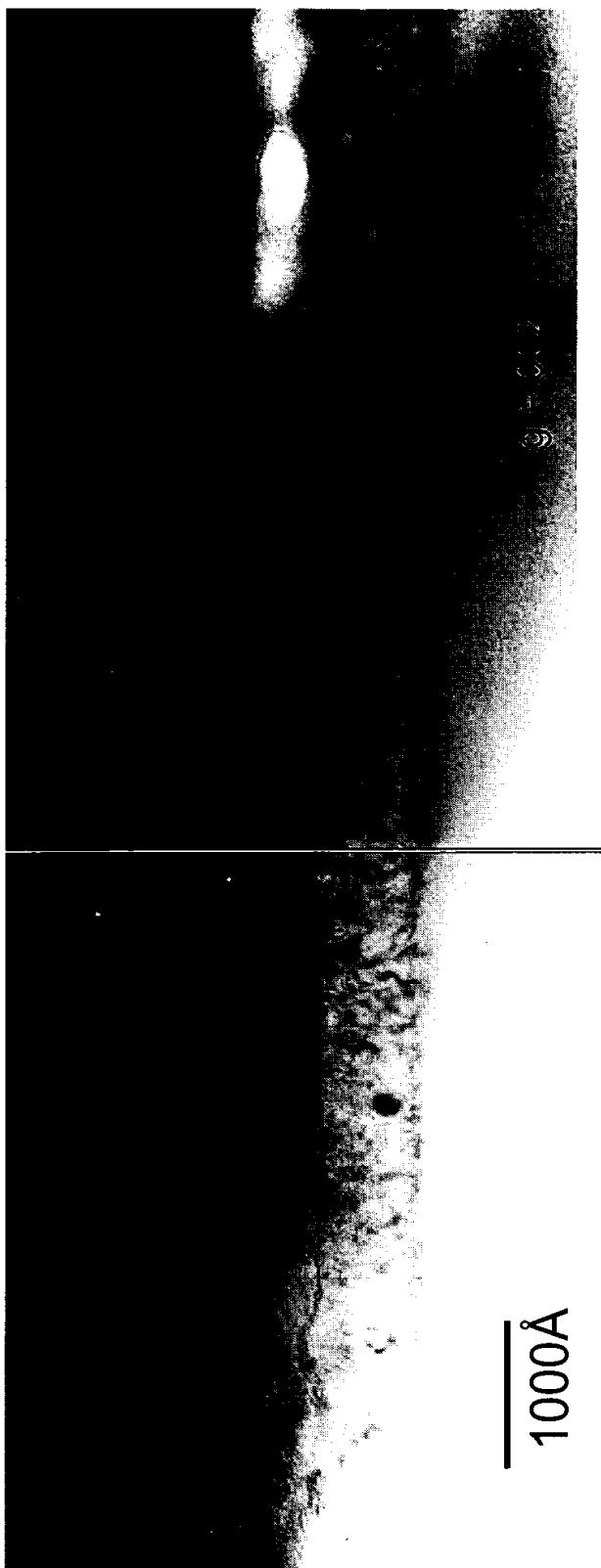


Fig. 11(b)



Ga-rich region

Fig. 12

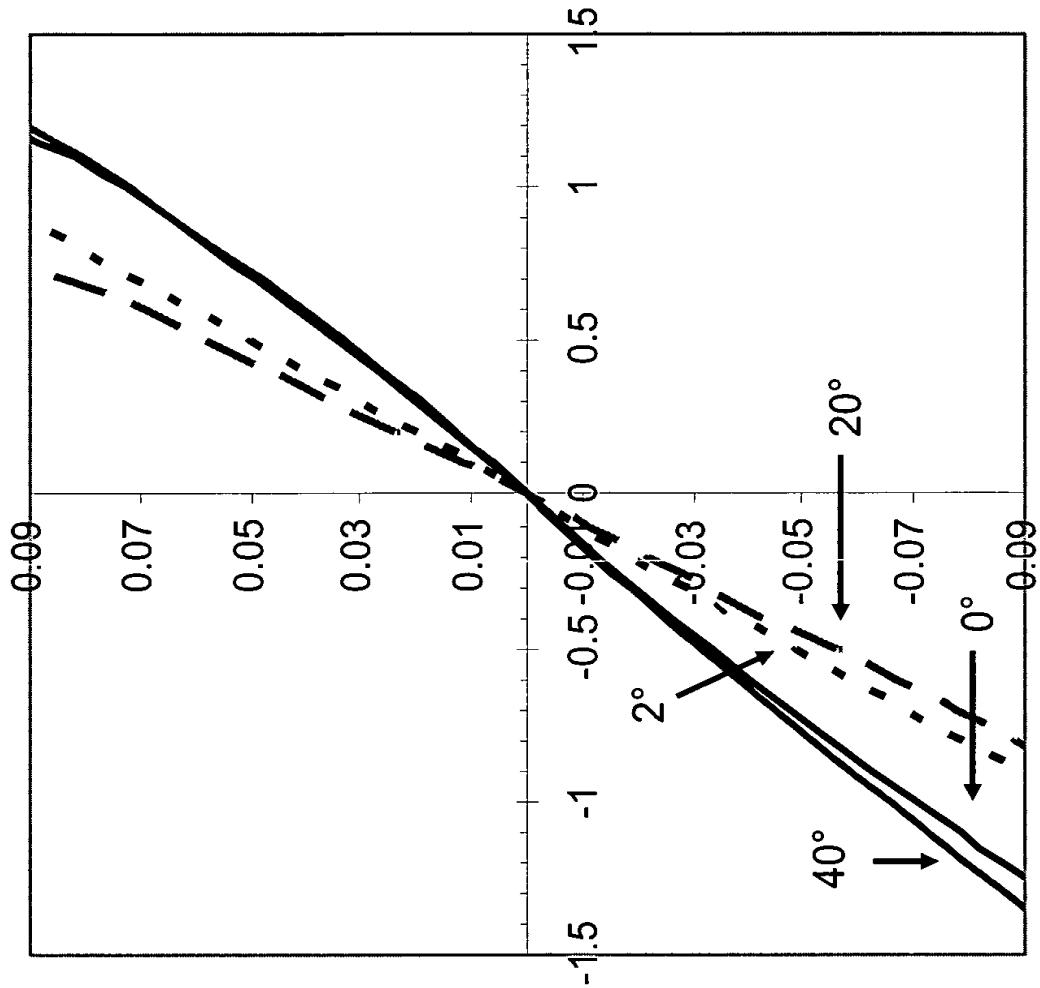


Fig. 13

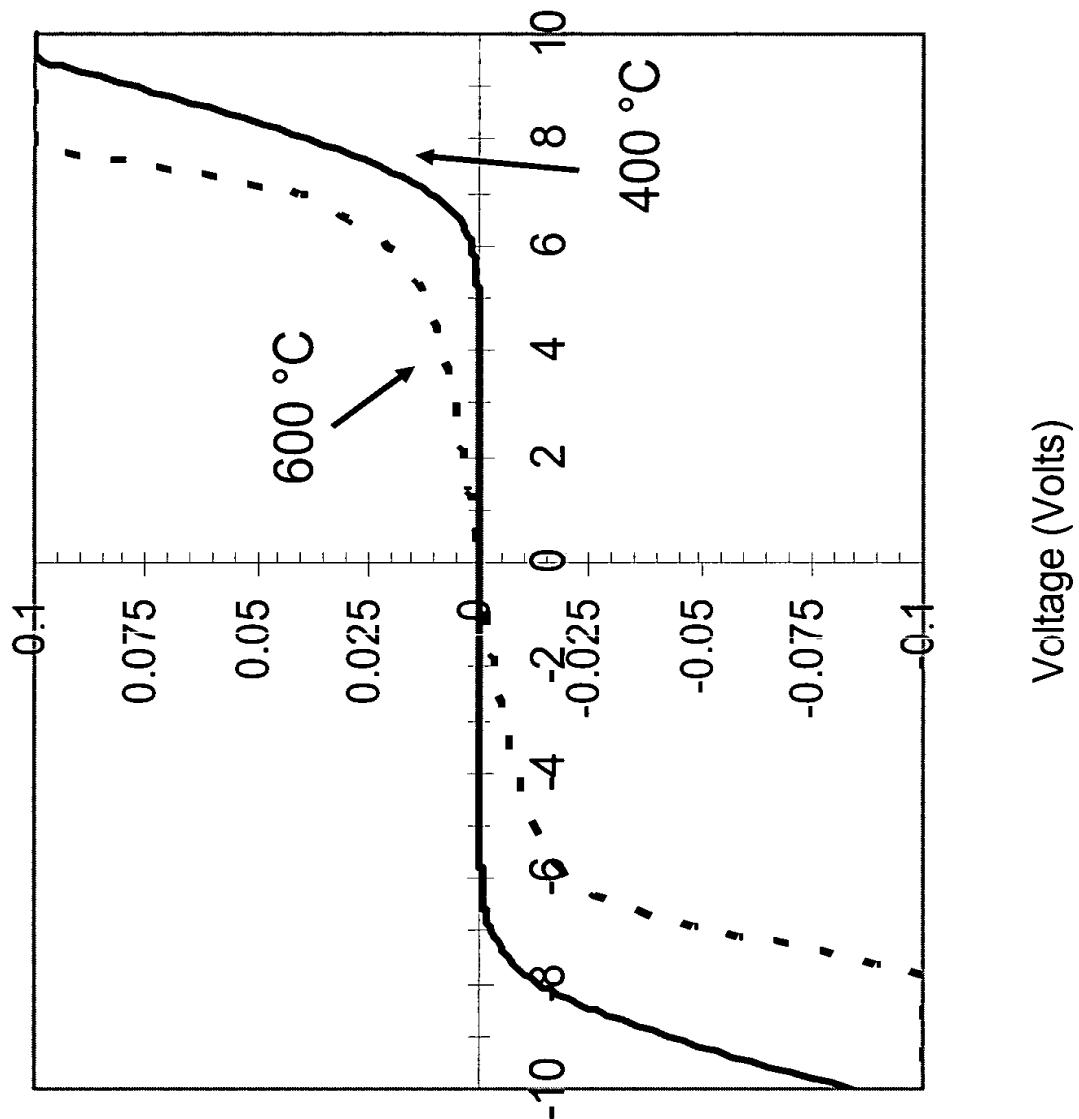


Fig. 14

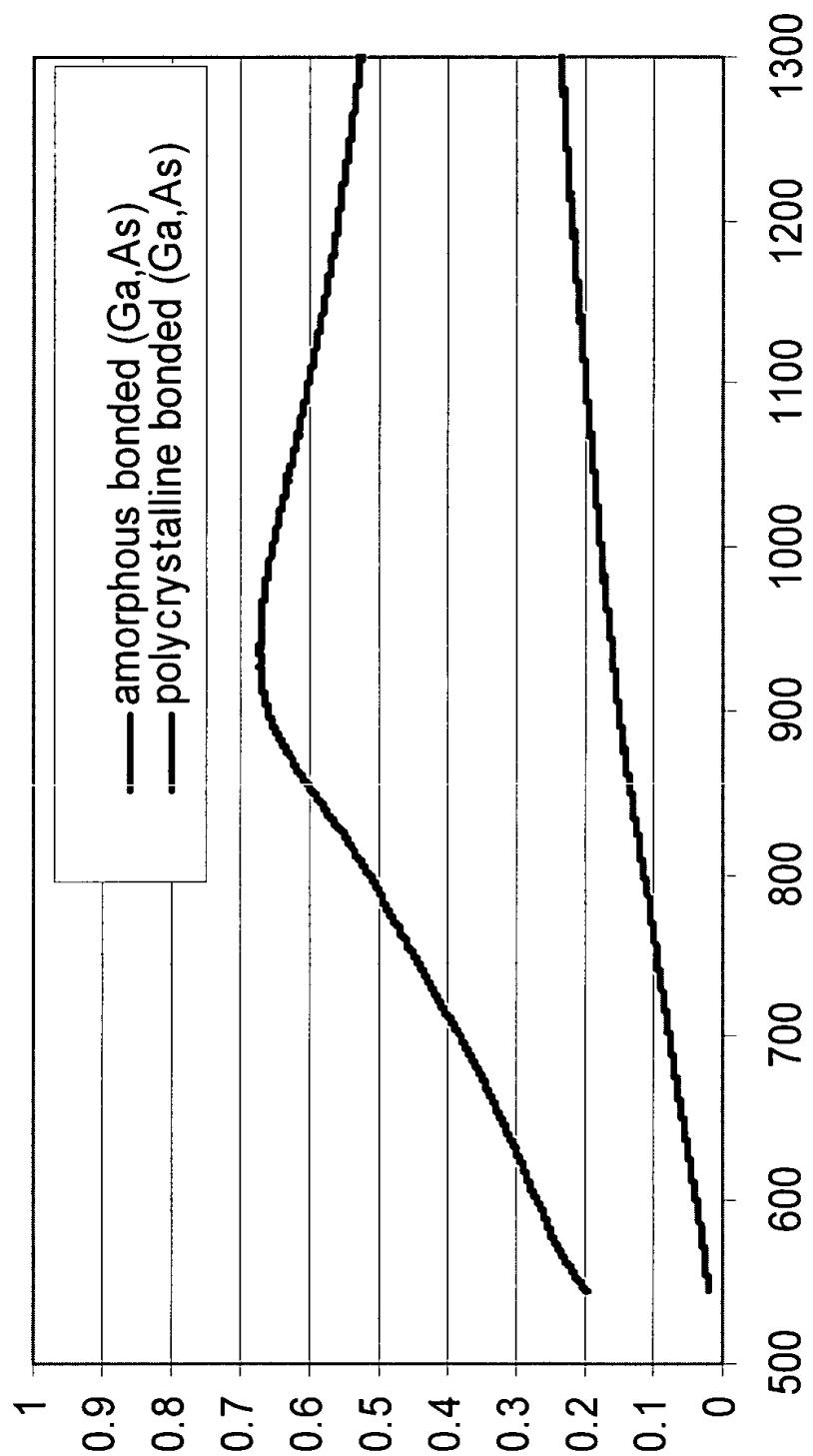


Fig. 15

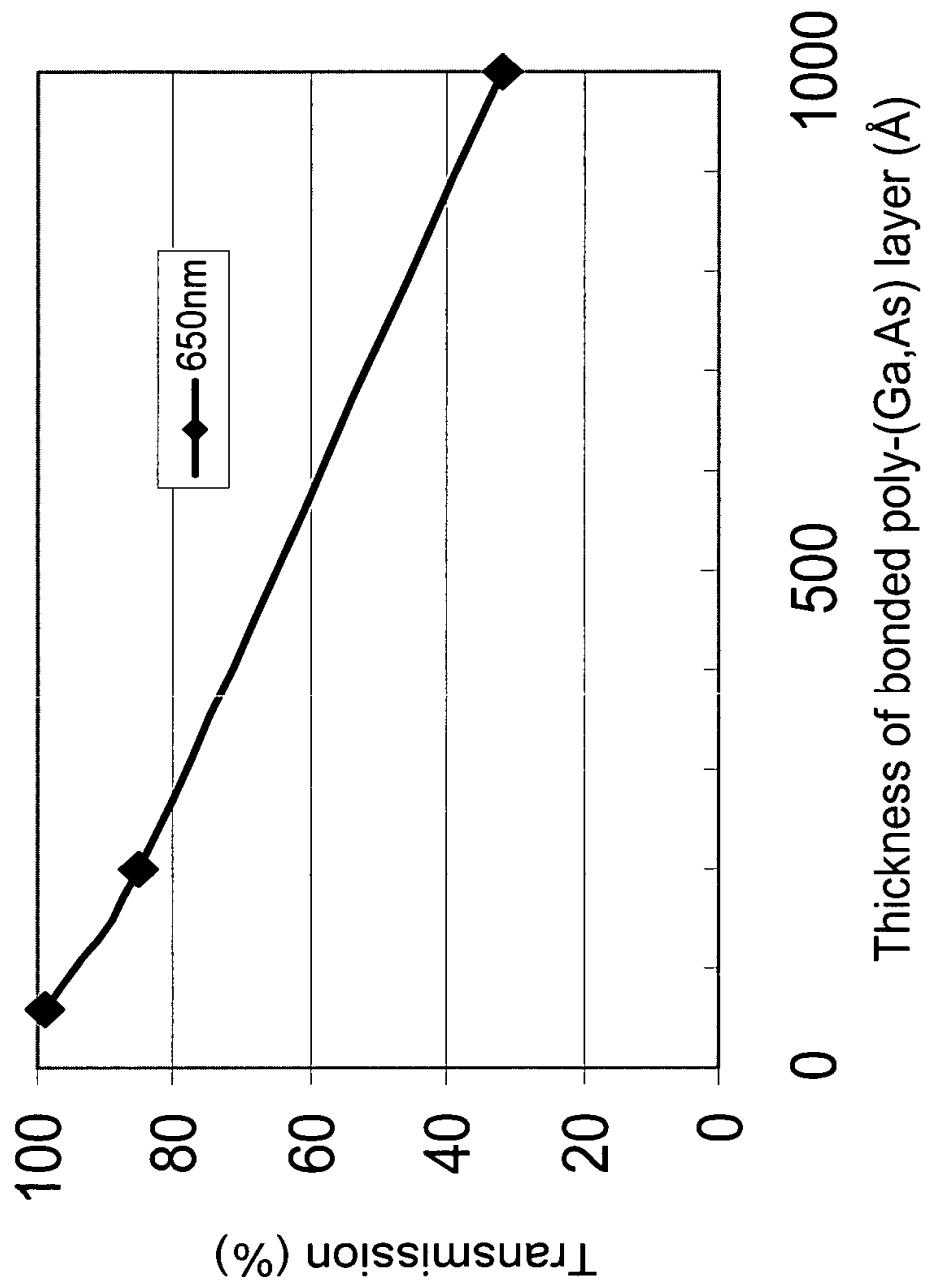


Fig. 16

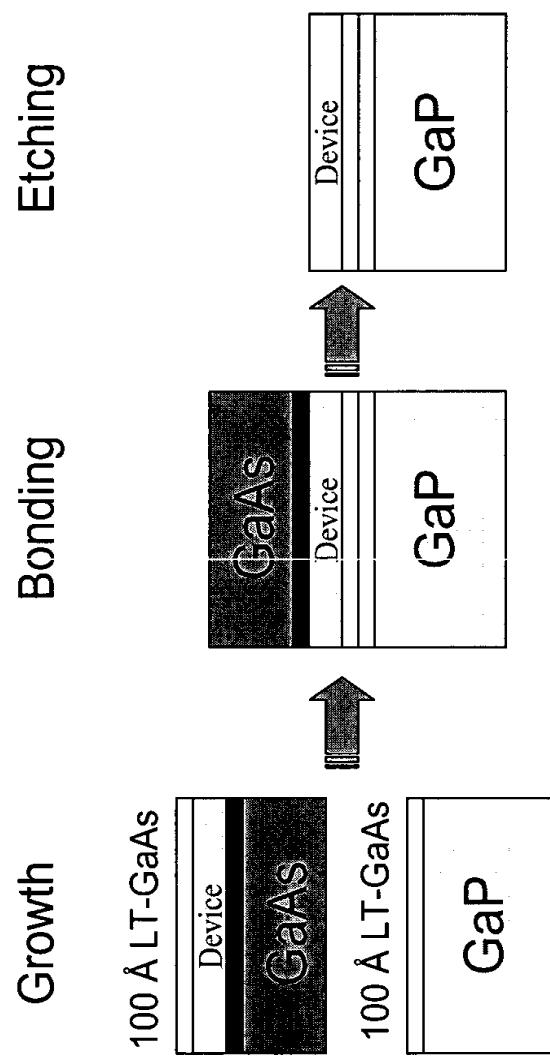


Fig. 17

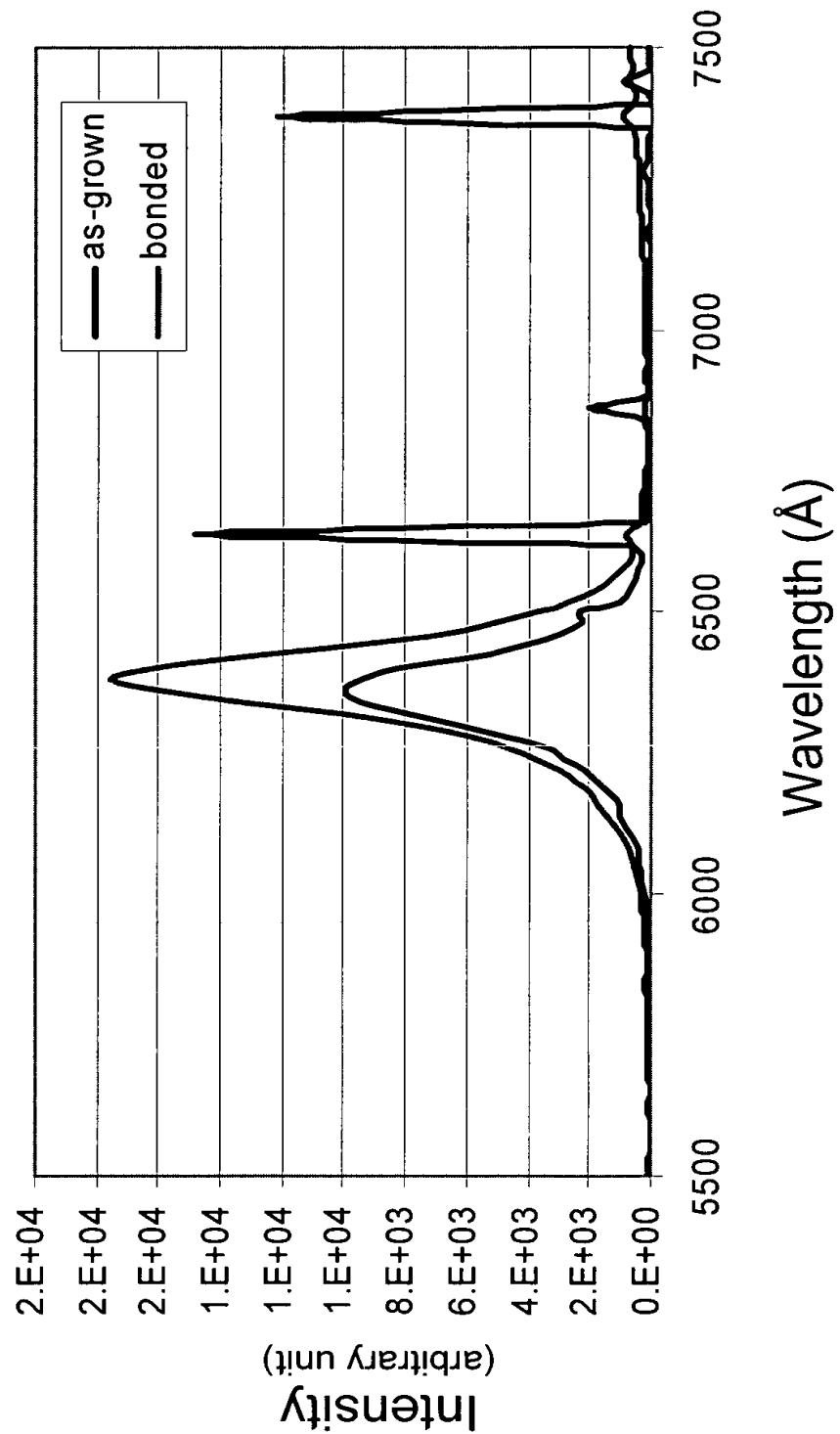


Fig. 18

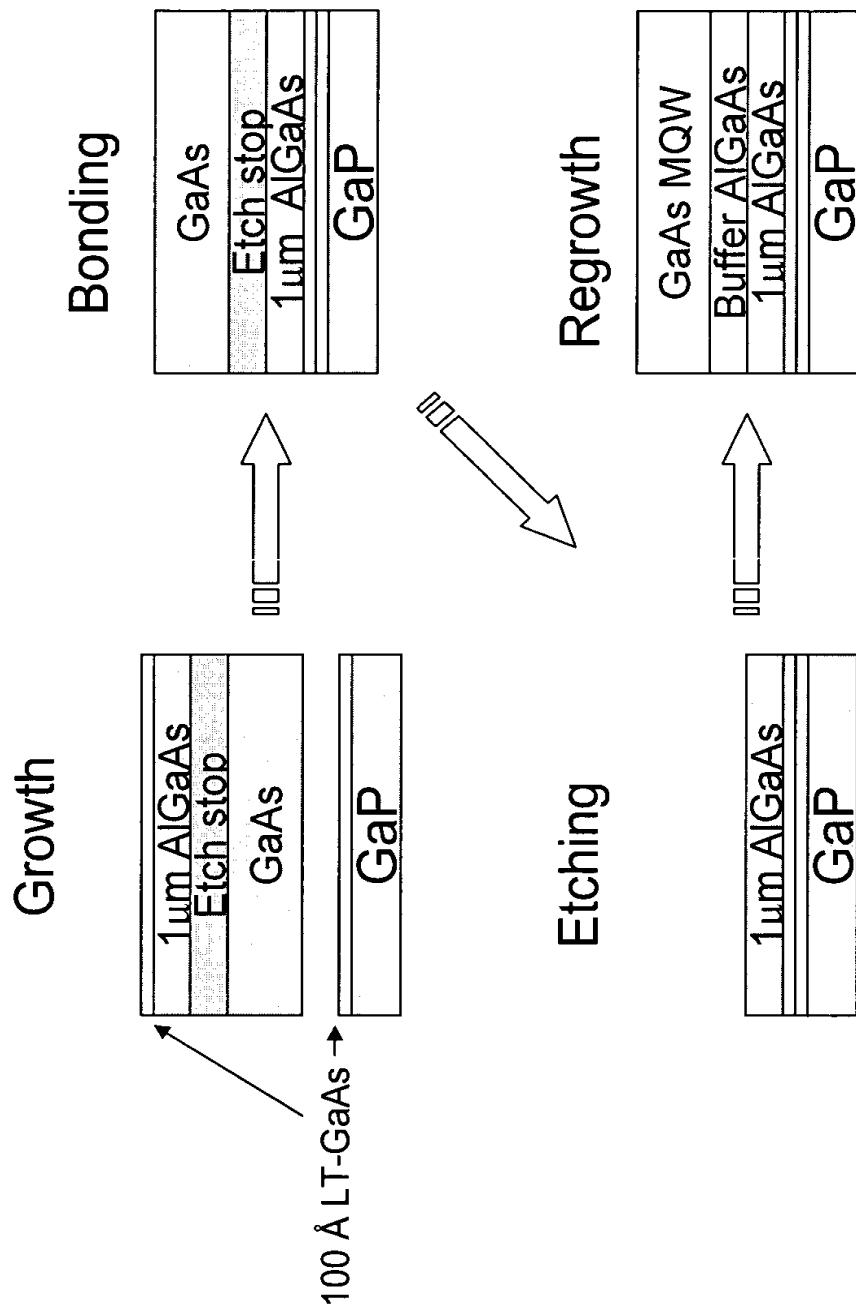


Fig. 19

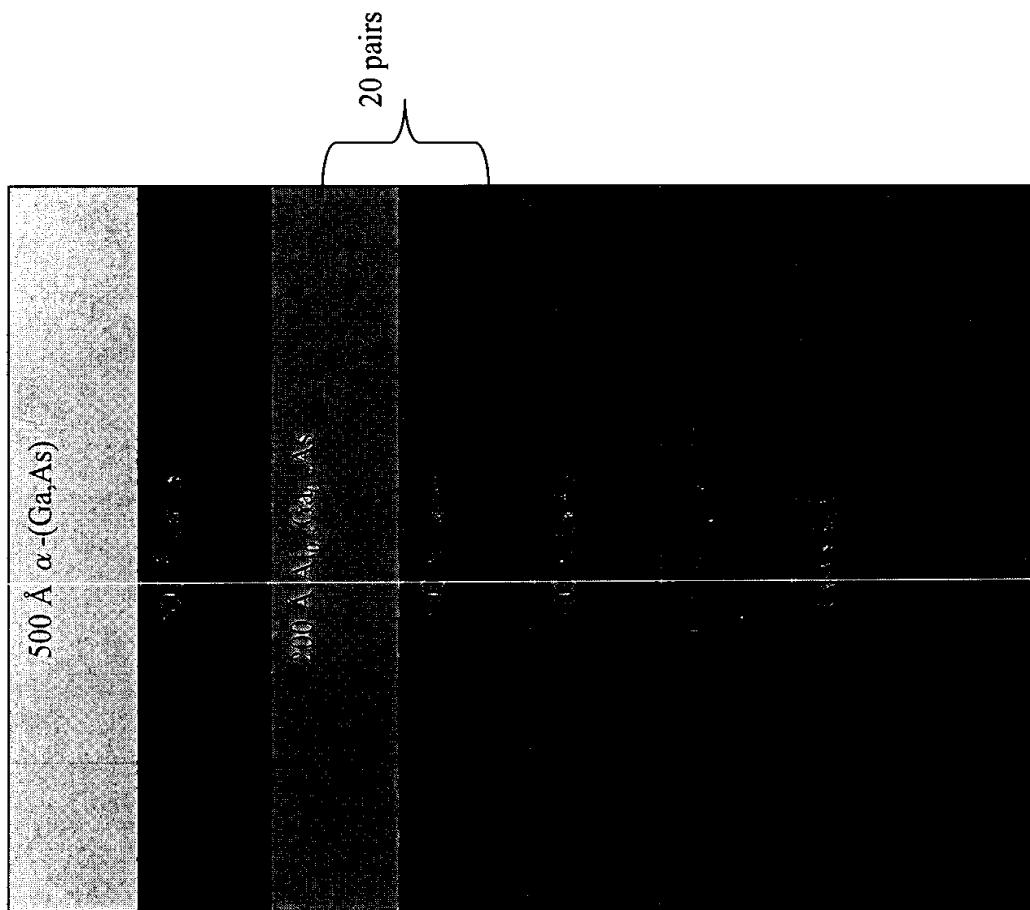


Fig. 20(a)

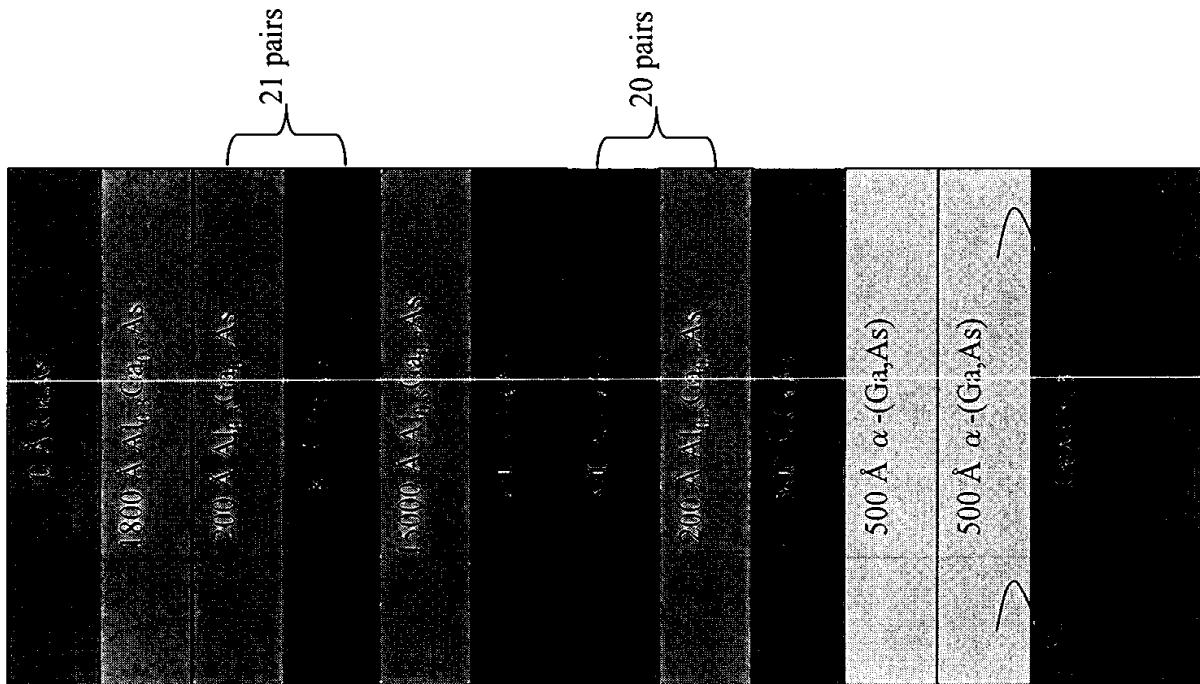


Fig. 20(b)

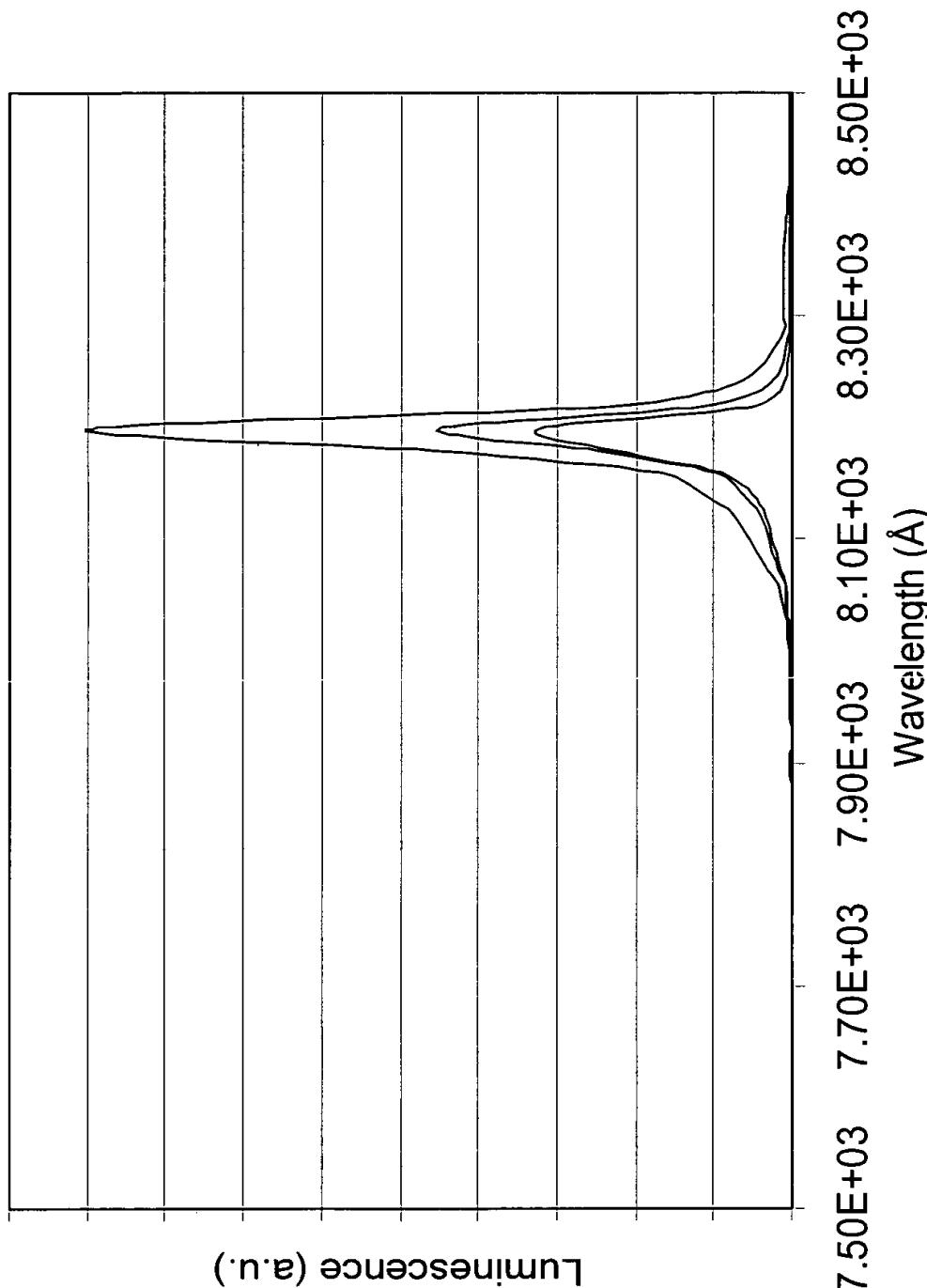


Fig. 21

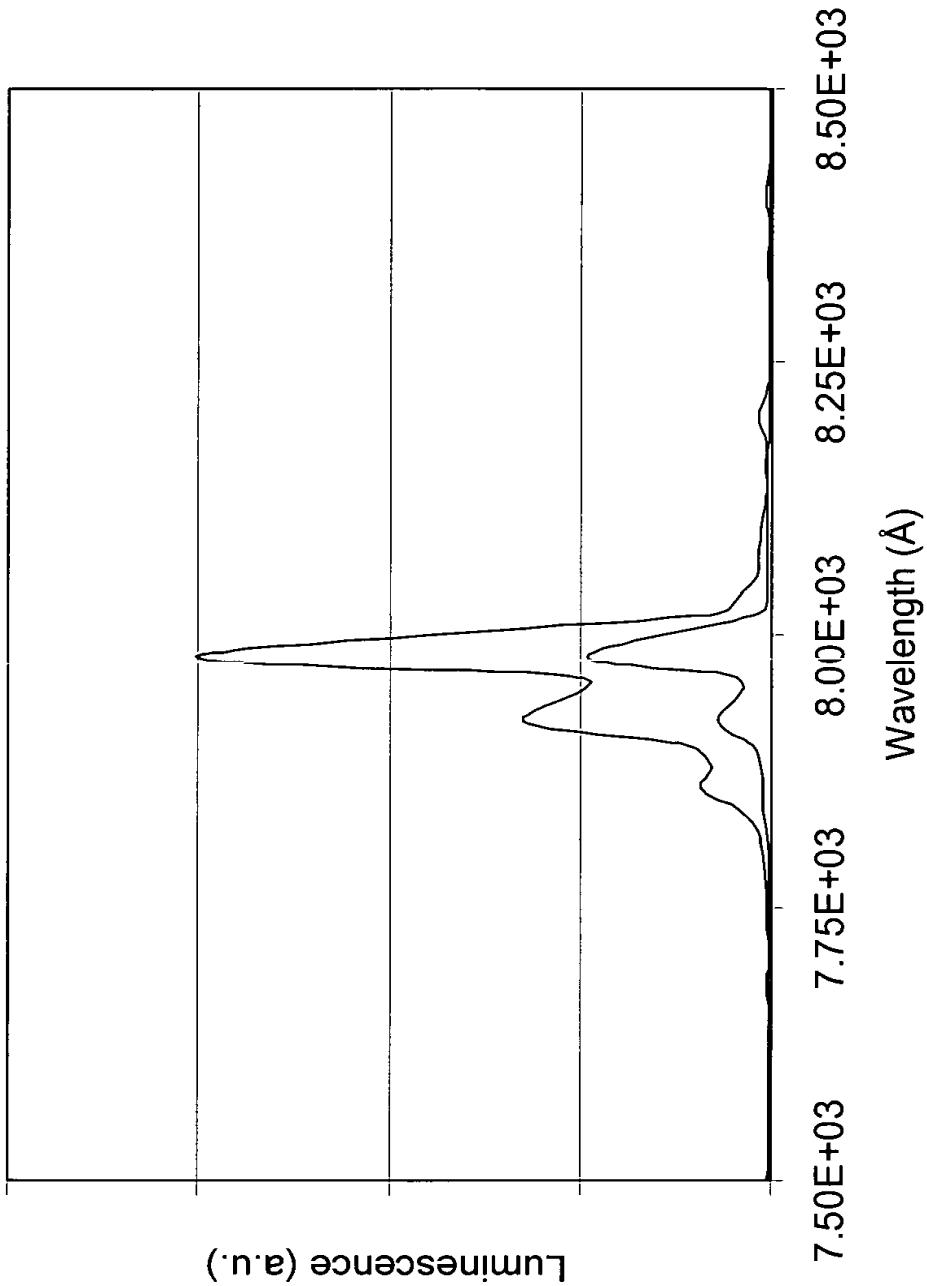


Fig. 22

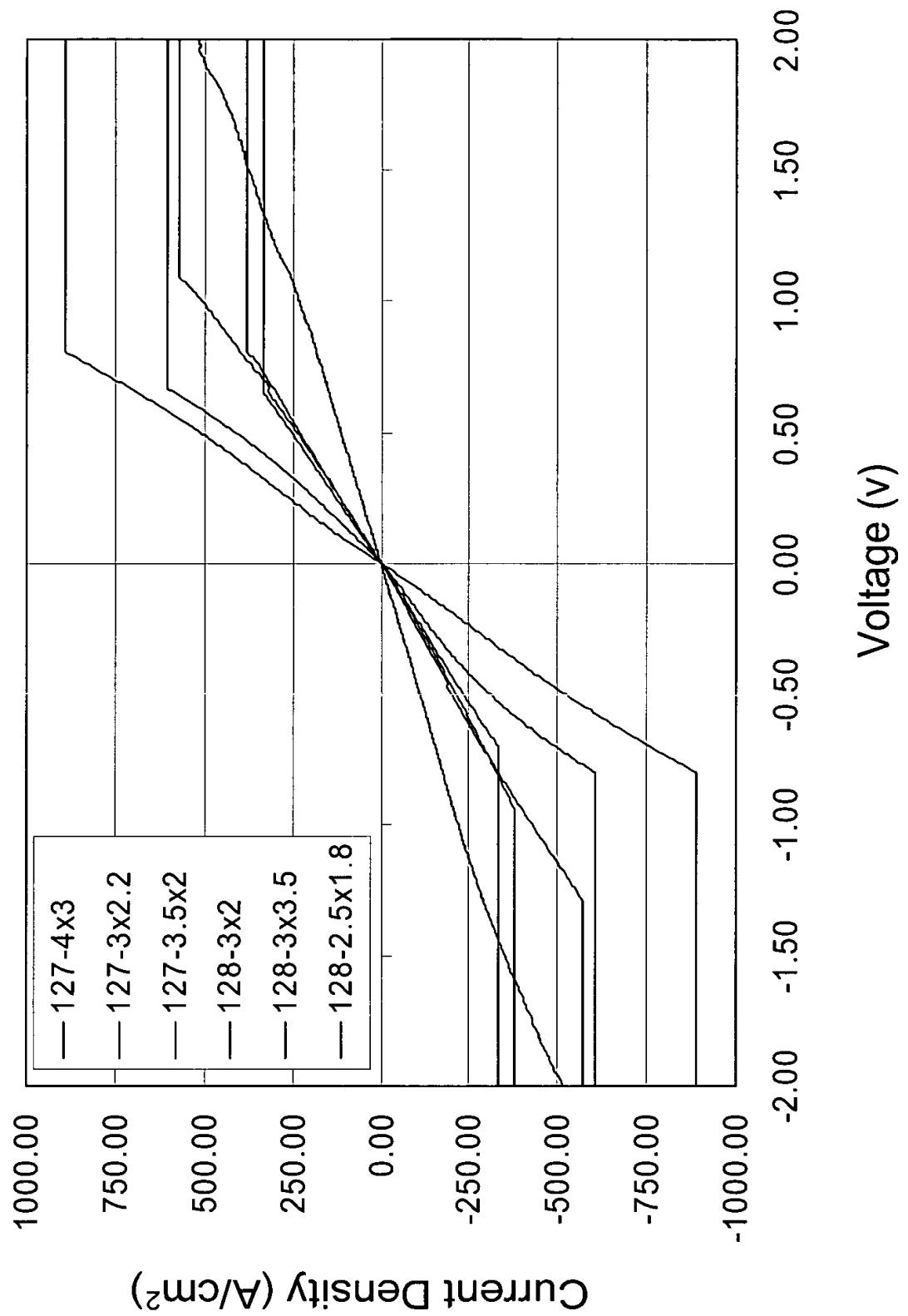


Fig. 23